



#### 30V NPN MEDIUM POWER TRANSISTOR IN SOT223

#### **Features**

- BV<sub>CEO</sub> > 30V
- I<sub>C</sub> = 1A High Continuous Current
- I<sub>CM</sub> = 4A Peak Pulse Current
- Low Saturation Voltage
- Complementary PNP Type: FZT589
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

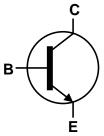
#### **Mechanical Data**

- Case: SOT223
- Case material: Molded Plastic. "Green" Molding Compound;
   UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

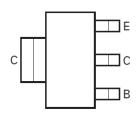




Top View



Device Symbol



Top View Pin-Out

#### Ordering Information (Notes 4 & 5)

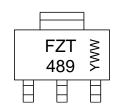
Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT489TA	AEC-Q101	FZT489	7	12	1,000
FZT489QTA	Automotive	FZT489	7	12	1.000

Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

#### **Marking Information**

SOT223



FZT 489 = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 5= 2015) WW or  $\overline{W}W$  = Week Code (01~53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	50	V
Collector-Emitter Voltage	$V_{\sf CEO}$	30	V
Emitter-Base Voltage	$V_{EBO}$	7	V
Continuous Collector Current	Ic	1	Α
Base Current	I <sub>B</sub>	200	mA
Peak Pulse Current	I <sub>CM</sub>	4	Α

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 6)		3.0	W	
Power Dissipation	(Note 7)	D-	2.0		
Power Dissipation	(Note 8)		1.6	VV	
	(Note 9)		1.2	]	
	(Note 6)		41.7		
Thermal Resistance, Junction to Ambient	(Note 7)		62.5		
Thermal Resistance, Junction to Ambient	(Note 8)	$R_{ hetaJA}$	78.1	°C/W	
	(Note 9)		104		
Thermal Resistance Junction to Lead (Note 10)		$R_{ hetaJL}$	19.4		
Operating and Storage Temperature Range	$T_{J,}T_{STG}$	-55 to +150	°C		

# ESD Ratings (Note 11)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

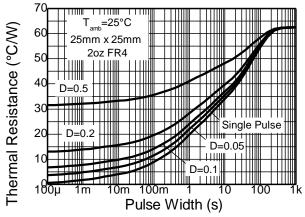
Notes:

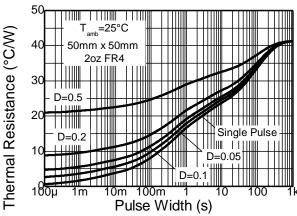
- 6. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

  7. Same as Note 6, except the device is mounted on 25mm x 25mm 2oz copper.
- 8. Same as Note 6, except the device is mounted on 25mm x 25mm 1oz copper.
- Same as Note 6, except the device is mounted on an inimum recommended pad layout.
   Thermal resistance from junction to solder-point (at the end of the collector lead).
   Refer to JEDEC specification JESD22-A114 and JESD22-A115.



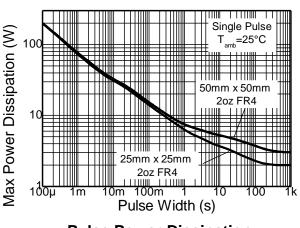
### **Thermal Characteristics and Derating Characteristics**



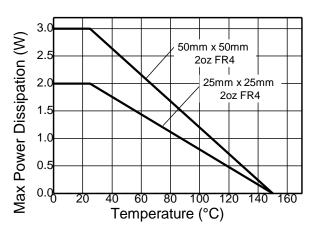


**Transient Thermal Impedance** 

**Transient Thermal Impedance** 



**Pulse Power Dissipation** 



**Derating Curve** 





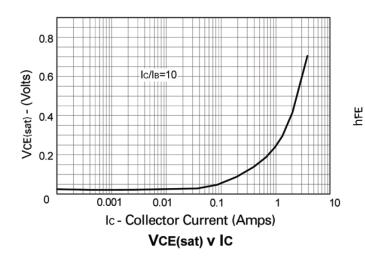
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

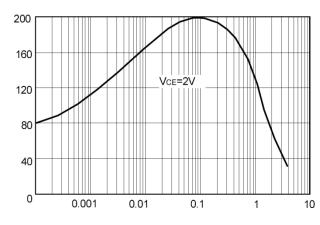
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	50	_	_	V	I <sub>C</sub> = 100μA
Collector-Emitter Breakdown Voltage (Note 12)	BV <sub>CEO</sub>	30	_	_	V	I <sub>C</sub> = 10mA
Emitter-Base Breakdown Voltage	$BV_EBO$	7	_	_	V	$I_E = 100\mu A$
Collector Cut-Off Current	I <sub>CBO</sub>	_	_	100	nA	V <sub>CB</sub> = 30V
Collector Cut-Off Current	I <sub>CES</sub>	_	_	100	nA	V <sub>CE</sub> = 30V
Emitter Cut-Off Current	I <sub>EBO</sub>	_	_	100	nA	V <sub>EB</sub> = 4V
Collector-Emitter Saturation Voltage (Note 12)	V <sub>CE(sat)</sub>	_ _	_ _	0.3 0.6	V	I <sub>C</sub> = 1A, I <sub>B</sub> = 100mA I <sub>C</sub> = 2A, I <sub>B</sub> = 200mA
Base-Emitter Saturation Voltage (Note 12)	V <sub>BE(sat)</sub>	_	_	1.1	V	I <sub>C</sub> = 1A, I <sub>B</sub> = 100mA
Base-Emitter Turn-On Voltage (Note 12)	V <sub>BE(on)</sub>	_	_	1.0	V	I <sub>C</sub> = 1A, V <sub>CE</sub> = 2V
DC Current Gain (Note 12)	h <sub>FE</sub>	100 100 60 20	- - -	300 - -	-	I <sub>C</sub> = 1mA, V <sub>CE</sub> = 2V I <sub>C</sub> = 1A, V <sub>CE</sub> = 2V I <sub>C</sub> = 2A, V <sub>CE</sub> = 2V I <sub>C</sub> = 4A, V <sub>CE</sub> = 2V
Current Gain-Bandwidth Product	f⊤	150	-	-	MHz	$V_{CE} = 10V, I_{C} = 50mA$ f = 100MHz
Output Capacitance	$C_{obo}$	=	=	10	pF	V <sub>CB</sub> = 10V, f = 1MHz

Note: 12. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.

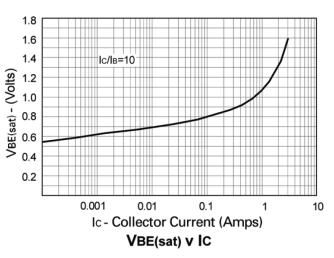


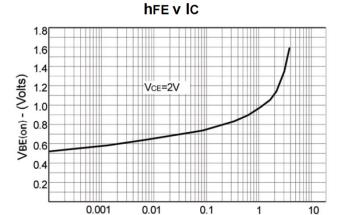
### Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)





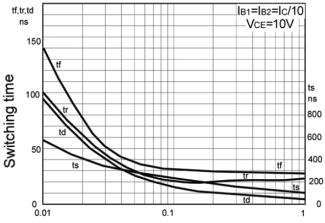
Ic - Collector Current (Amps)





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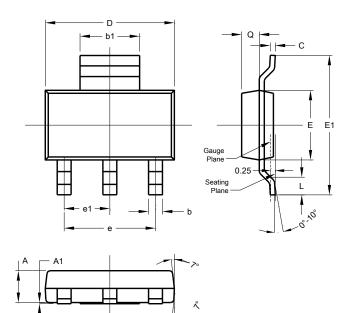
VBE(on) v IC





### **Package Outline Dimensions**

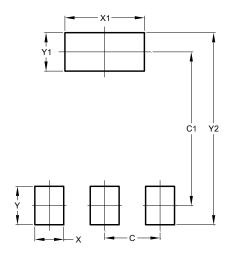
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
E	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00





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